

NPN Silicon Epitaxial Planar Transistor

ELECTRICAL CHARACTERISTICS @ Ta=25 unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\text{ A}, I_E=0$	60			V

Collector-emitter breakdown voltage $V_{(BR)CEO}$ $I_C=1\text{mA}, I_B=0$

TYPICAL CHARACTERISTICS

